Docket No.

292759US0PC7

OTP E 4208 OCT 0 3 2006

MAIL STOP PCT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Frederic MAZEN, et al.

SERIAL NO:

10/584,053

GAU:

FILED:

June 22, 2006

EXAMINER:

FOR:

METHOD FOR THE ORGANISED GROWTH OF NANOSTRUCTURES

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references cited in the International Search Report and listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- □ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449
(Modified)

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SERIAL NO. 10/584,053

APPLICANT

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LIST OF REFERENCES CITED BY APPLICANT										
	FILING DATE				GROUP					
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				U.S. PATENT DOCUMENTS		***************************************	•			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS		ILING DATE APPROPRIATE		
	AA	5 935 454	08/10/1999	TADA et al.						
	AB	4 908 226	03/13/1990	KUBENA et al.						
	AC	2003 0157744	08/21/2003	SCHLAF						
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		NUMBER	DATE	COUNTRY		YES NO				
	AO									
	AP									
	AQ									
	AR									
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-	AT	KUBENA R. L. et al., "SELECTIVE AREA NUCLEATION FOR METAL CHEMICAL VAPOR DEPOSITION USING FOCUSED ION BEAMS", JOURNAL OF VACUUM SCIENCE AND TECHNOLOGY, Vol. B6 (6), pages1865-1868, XP 000133336, 1988								
	AU	GERLACH R., "FOCUSED ION BEAM METHODS OF NANOFABRICATION: ROOM AT THE BOTTOM", PROCEEDINGS OF SPIE, Vol. 4510, pages 96-106, XP 008035414, 2001								
	AV	SCHMUKI P. et al., "SELECTIVE ELECTRODEPOSITION OF MICROPATTERNS ON PREDEFINED SURFACE DEFECTS ON P-Si (100)", JOURNAL OF ELECTROCHEMICAL SOCIETY, Vol. 148, pages 177-182, 2001								
	AW	BARON T. et al., "SILICON QUANTUM DOT NUCLEATION ON Si3 N4, SiO2, AND SiOx Ny SUBSTRATES FOR NANOELECTRONIC DEVICES", JOURNAL OF CRYSTAL GROWTH, Vol. 209, pages 1004-1008, 2000								
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	AY									
	AZ		, ,		Addi	Additional References sheet(s) attached				
Examiner					Date Cor	nsidered		-		

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

U.S. PCT Application Serial No: 10/584,053

Filed: June 22, 2006 Frederic MAZEN, et al. Docket No. 292759 US

STATEMENT OF RELEVANCY

- 1) References AA-AD & AT-AU have been cited in the International Search Report. A copy of these references is being submitted herewith.
- 2) References have been cited in the corresponding Search Report. A copy of these references is being submitted herewith.
- 3) References AV-AX are discussed in the specification. A copy of these references is being submitted herewith.
- 4) References are additional prior art known to Applicant. A copy of these references is being submitted herewith.